

Optimization of thin film solar cells through defect characterization

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Defects in SemiConductors

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Need for solar cells: space research, oil crisis, cleaner energy, stabler energy

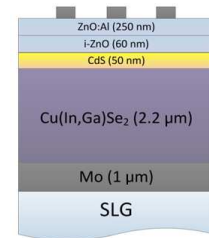
Evolution towards thin film:

Si solar cell absorbs relatively poor → thick absorber needed (~100 μm)



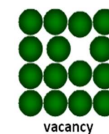
CuInGaSe₂ material has high absorption coefficient → thin absorber (~2 μm)

Advantage: lower cost, flexible cell

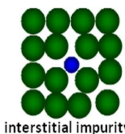


Problem: defects in absorber lattice reduce efficiency

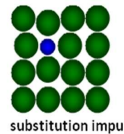
→ Research DiSC: defect characterization



vacancy



interstitial impurity

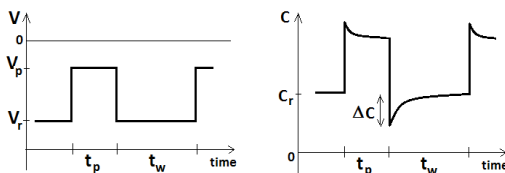


substitution impurity

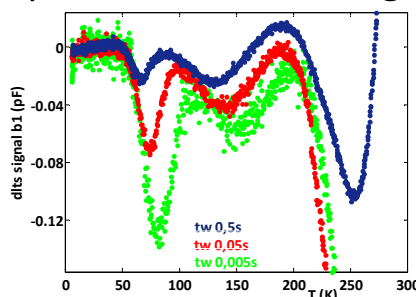
Research methods:

Deep Level Transient Spectroscopy

→ measure capacitance transient after voltage pulse for different temperature

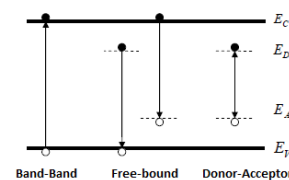


→ deep defects, contact signal

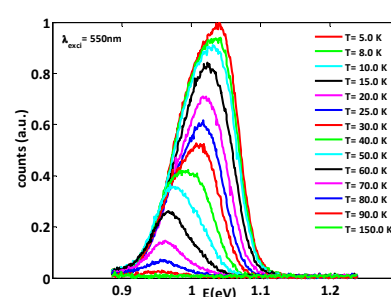


Photoluminescence

→ measure light of radiative recombination when cell is illuminated



→ shallow defects



Conclusion: by controlling defects in thin film solar cells the efficiency can be enhanced.